DS4190-2.2

## DS2009SF RECTIFIER DIODE

**APPLICATIONS** 

**KEY PARAMETERS** 

V<sub>RRM</sub> 4800V I<sub>F(AV)</sub> 1105A I<sub>ESM</sub> 20500A

- Rectification.
- Freewheel Diode.
- DC Motor Control.
- Power Supplies.
- Welding.
- Battery Chargers.

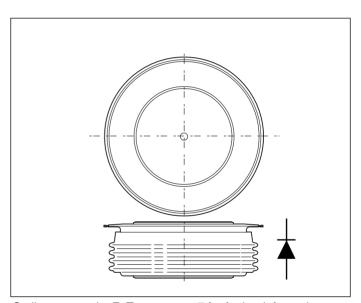
#### **FEATURES**

- Double Side Cooling.
- High Surge Capability.

#### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Reverse Voltage V	Conditions
DS2009SF48	4800	$V_{RSM} = V_{RRM} + 100V$
DS2009SF47	4700	NOW KKW
DS2009SF46	4600	
DS2009SF45	4500	
DS2009SF44	4400	
DS2009SF43	4300	

Lower voltage grades available.



Outline type code: F. Turn to page 7 for further information.

#### **CURRENT RATINGS**

Symbol	Parameter	Conditions	Max.	Units			
Double Side Cooled							
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 100°C	1105	А			
I <sub>F(RMS)</sub>	RMS value	T <sub>case</sub> = 100°C	1735	А			
I <sub>F</sub>	Continuous (direct) forward current	$T_{\text{case}} = 100^{\circ}\text{C}$	1580	А			
Single Side Cooled (Anode side)							
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 100°C		А			
I <sub>F(RMS)</sub>	RMS value	$T_{\text{case}} = 100^{\circ}\text{C}$	1145	А			
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 100°C	960	А			

## **DS2009SF**

## **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; T <sub>case</sub> = 150°C	16.5	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 50\% V_{RRM} - 1/4 sine$	1.35 x 10 <sup>6</sup>	A²s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10ms half sine; T <sub>case</sub> = 150°C	20.5	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	$V_R = 0$	2.125 x 10 <sup>6</sup>	A <sup>2</sup> s

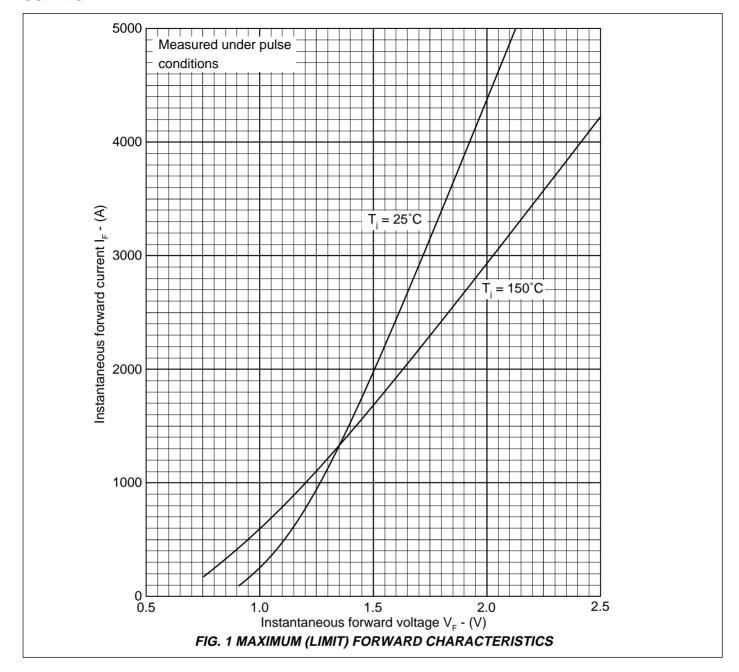
## THERMAL AND MECHANICAL DATA

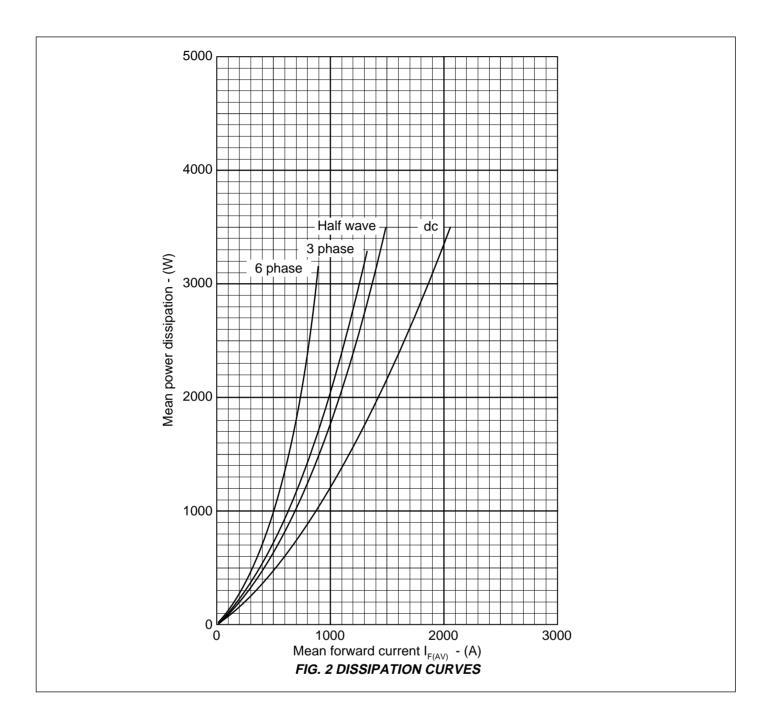
Symbol	Parameter	Conditions		Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance - junction to case	Double side cooled	dc	-	0.022	°C/W
		Single side cooled	Anode dc	-	0.038	°C/W
			Cathode dc	-	0.052	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Clamping force 19.5kN with mounting compound	Double side	-	0.004	°C/W
			Single side	-	0.008	°C/W
_	Virtual junction temperature	On-state (conducting)	•	-	160	°C
T <sub>vj</sub>		Reverse (blocking)		-	150	°C
T <sub>stg</sub>	Storage temperature range			-55	175	°C
-	Clamping force			18.0	22.0	kN

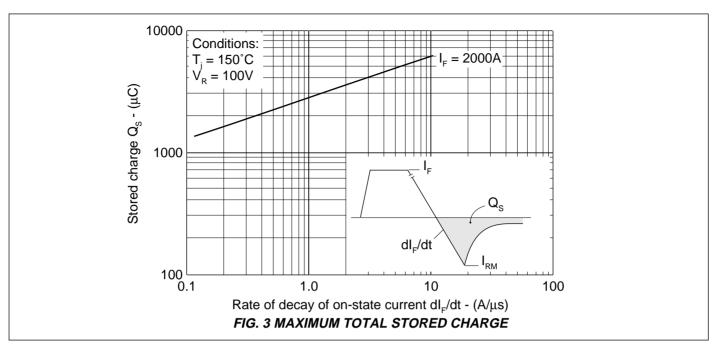
## **CHARACTERISTICS**

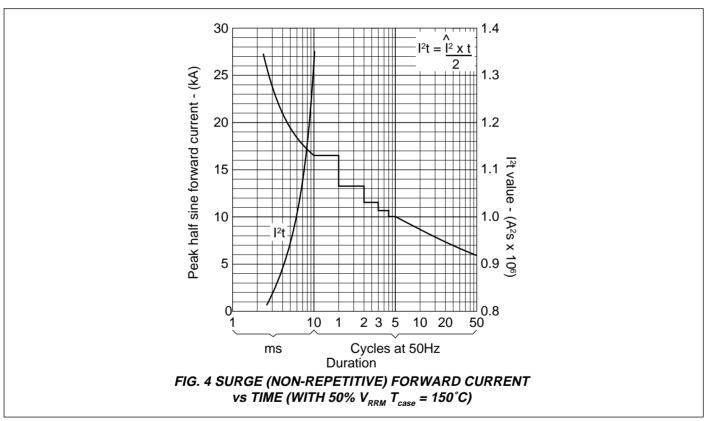
Symbol	Parameter	Conditions	Min.	Max.	Units
V <sub>FM</sub>	Forward voltage	At 3400A peak, T <sub>case</sub> = 25°C	-	1.8	V
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 150°C	-	75	mA
Q <sub>s</sub>	Total stored charge	$I_F = 2000A$ , $dI_{RR}/dt = 3A/\mu s$ ,	-	4000	μС
I <sub>RM</sub>	Peak recovery current	$T_{case} = 150^{\circ}C, V_{R} = 100V$	-	115	А
V <sub>TO</sub>	Threshold voltage	At T <sub>vj</sub> = 150°C	-	0.84	V
r <sub>T</sub>	Slope resistance	At T <sub>vj</sub> = 150°C	-	0.383	mΩ

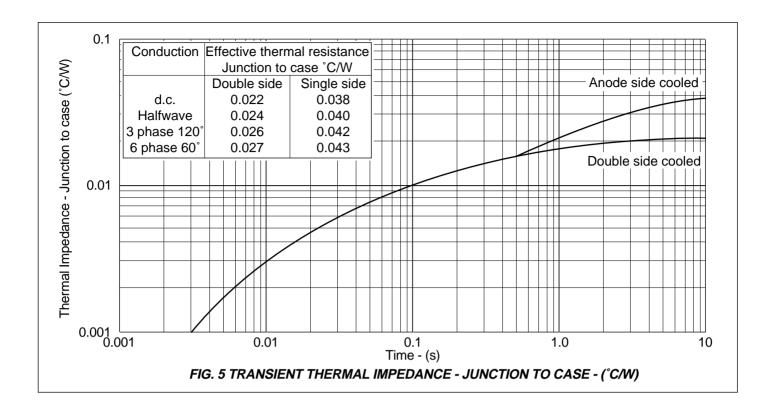
#### **CURVES**





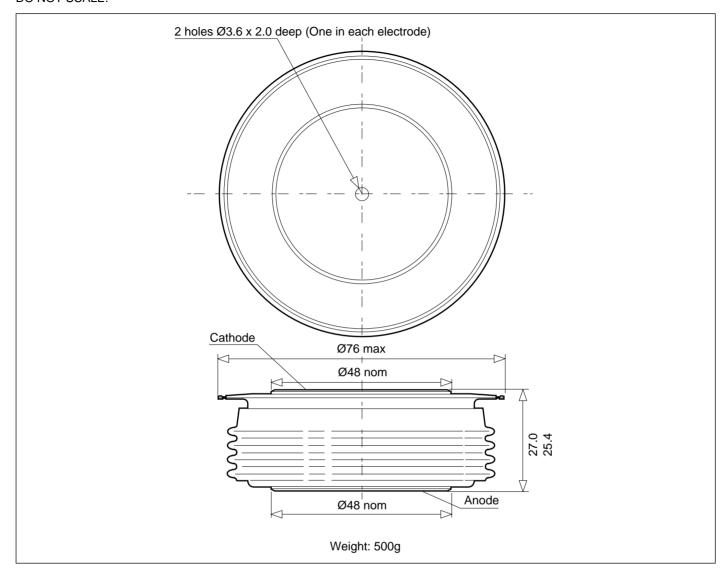






#### **PACKAGE DETAILS - F**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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